



N-Ch 30V Fast Switching MOSFETs



- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST20N03D Product Summary

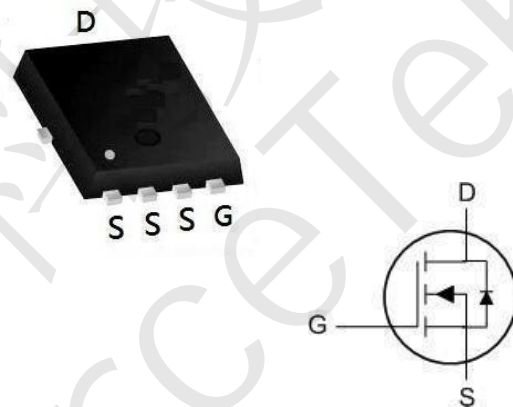
| BVDSS | RDSON | ID |
|-------|-------|-----|
| 30V | 15mΩ | 20A |

CST20N03D Description

The CST20N03D is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST20N03D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

CST20N03D PDFN3*3 Pin Configuration



CST20N03D Absolute Maximum Ratings

| Symbol | Parameter | Rating | | Units |
|-----------------------|--|------------|--------------|------------|
| | | 10s | Steady State | |
| V_{DS} | Drain-Source Voltage | 30 | | V |
| V_{GS} | Gate-Source Voltage | ± 20 | | V |
| $I_D@T_C=25^\circ C$ | Continuous Drain Current, $V_{GS}@ 10V^1$ | 20 | | A |
| $I_D@T_C=100^\circ C$ | Continuous Drain Current, $V_{GS}@ 10V^1$ | 8 | | A |
| I_{DM} | Pulsed Drain Current ² | 38 | | A |
| EAS | Single Pulse Avalanche Energy ³ | 28 | | mJ |
| I_{AS} | Avalanche Current | 13.8 | | A |
| $P_D@T_C=25^\circ C$ | Total Power Dissipation ⁴ | 5.5 | | W |
| T_{STG} | Storage Temperature Range | -55 to 175 | | $^\circ C$ |
| T_J | Operating Junction Temperature Range | -55 to 175 | | $^\circ C$ |

CST20N03D Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|-----------------|---|------|------|--------------|
| $R_{\theta JC}$ | Thermal Resistance Junction-Case ¹ | --- | 36 | $^\circ C/W$ |



CST20N03D Electrical Characteristics (T_J=25°C unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---|---|---|------|------|------|-------|
| Off Characteristic | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 30 | - | - | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} = 0V, | - | - | 1.0 | μA |
| I _{GSS} | Gate to Body Leakage Current | V _{DS} =0V, V _{GS} = ±20V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 1.0 | 1.5 | 2.5 | V |
| R _{DS(on)} | Static Drain-Source on-Resistance <small>note3</small> | V _{GS} =10V, I _D =5A | - | 15 | 20 | mΩ |
| | | V _{GS} =4.5V, I _D =3A | - | 21 | 29 | |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, f=1.0MHz | - | 490 | - | pF |
| C _{oss} | Output Capacitance | | - | 79 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 61 | - | pF |
| Q _g | Total Gate Charge | V _{DS} =15V, I _D =5.8A, V _{GS} =10V | - | 10 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 1.7 | - | nC |
| Q _{gd} | Gate-Drain("Miller") Charge | | - | 2.5 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-on Delay Time | V _{DS} =15V, I _D =3A, V _{GS} =10V, R _{REN} =3Ω | - | 6 | - | ns |
| t _r | Turn-on Rise Time | | - | 15 | - | ns |
| t _{d(off)} | Turn-off Delay Time | | - | 17 | - | ns |
| t _f | Turn-off Fall Time | | - | 17 | - | ns |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 9 | A |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 36 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} =0V, I _S =9A | - | - | 1.2 | V |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =5A, di/dt=100A/μs | - | 7 | - | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | | - | 2 | - | nC |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=6A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



CST20N03D Typical Performance Characteristics

Figure 1: Output Characteristics

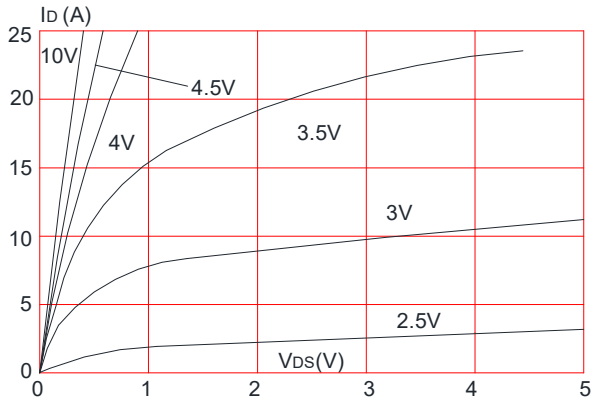


Figure 2: Typical Transfer Characteristics

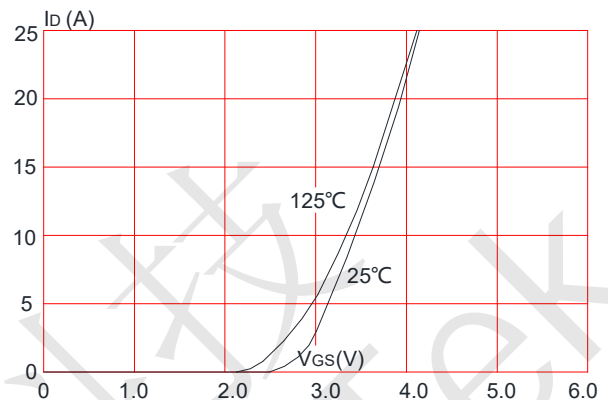


Figure 3: On-resistance vs. Drain Current

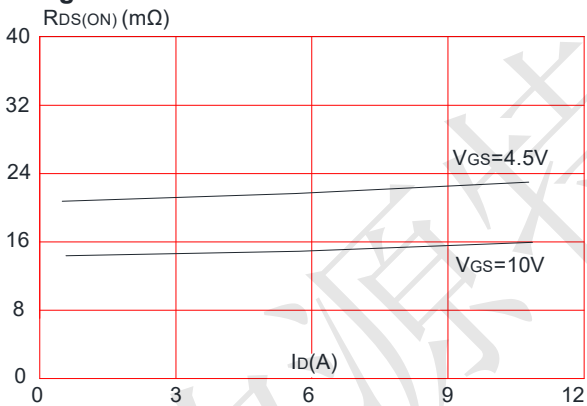


Figure 4: Body Diode Characteristics

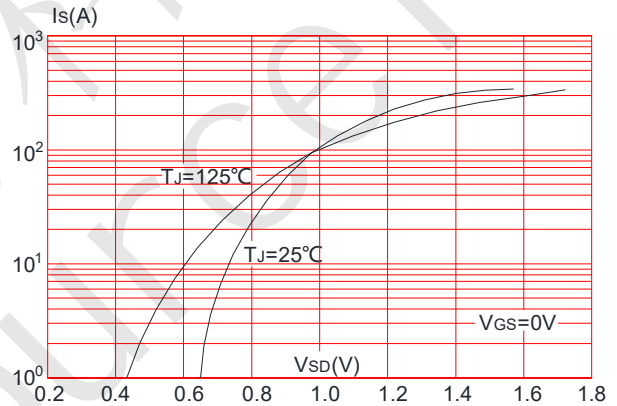


Figure 5: Gate Charge Characteristics

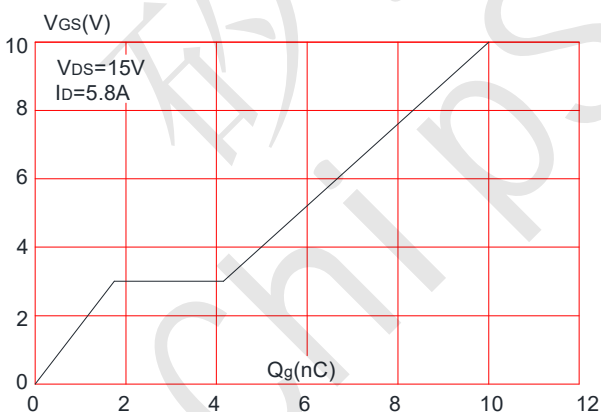


Figure 6: Capacitance Characteristics

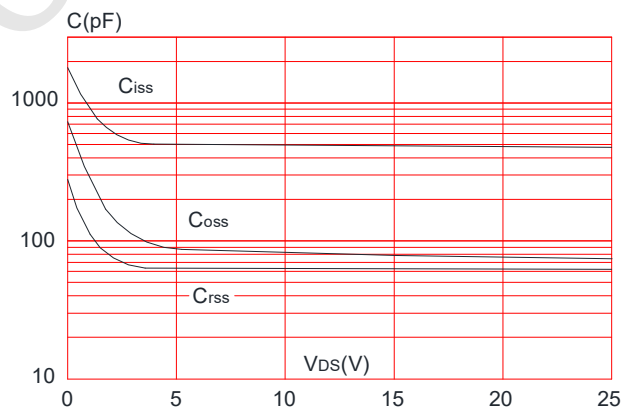




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

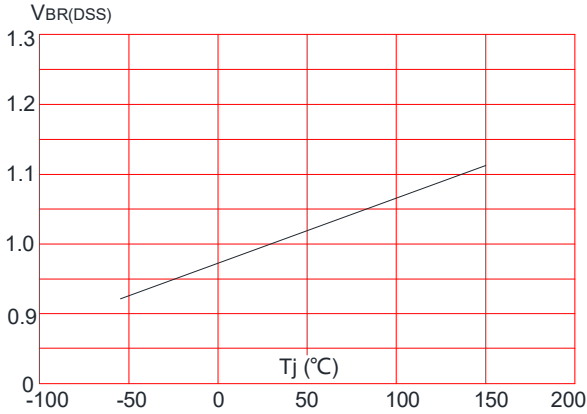


Figure 8: Normalized on Resistance vs. Junction Temperature

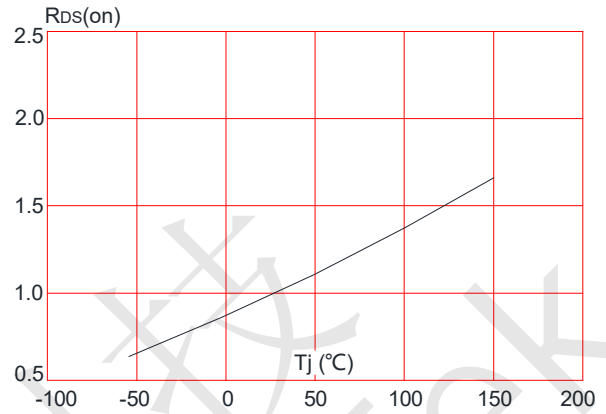


Figure 9: Maximum Safe Operating Area

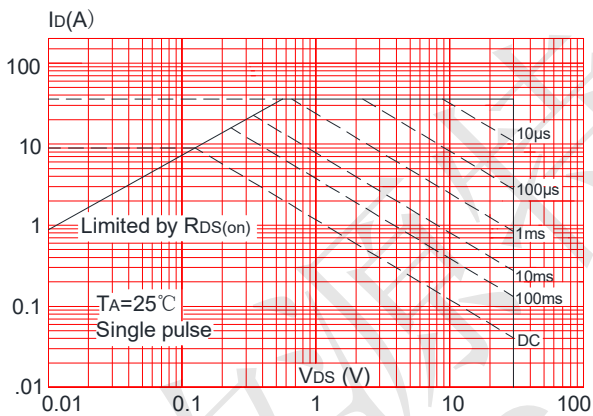


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

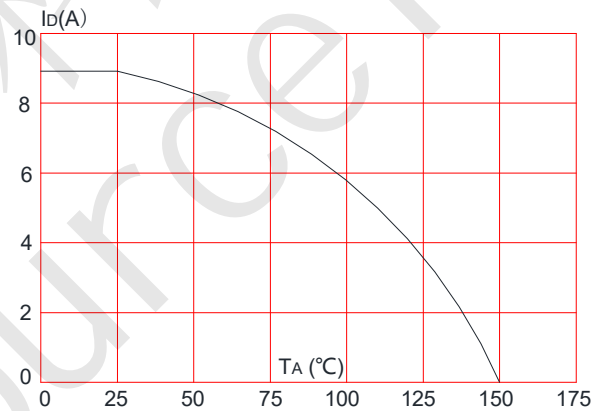
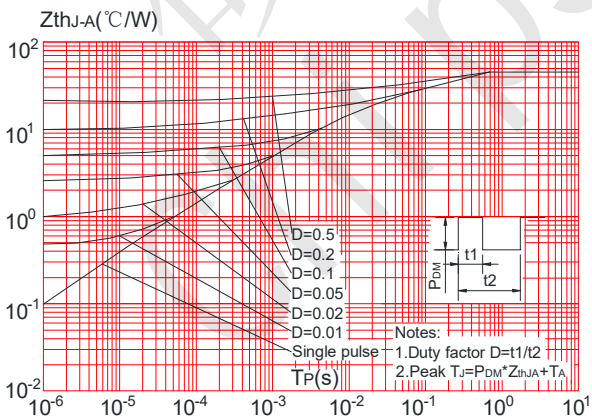


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





CST20N03D Test Circuit

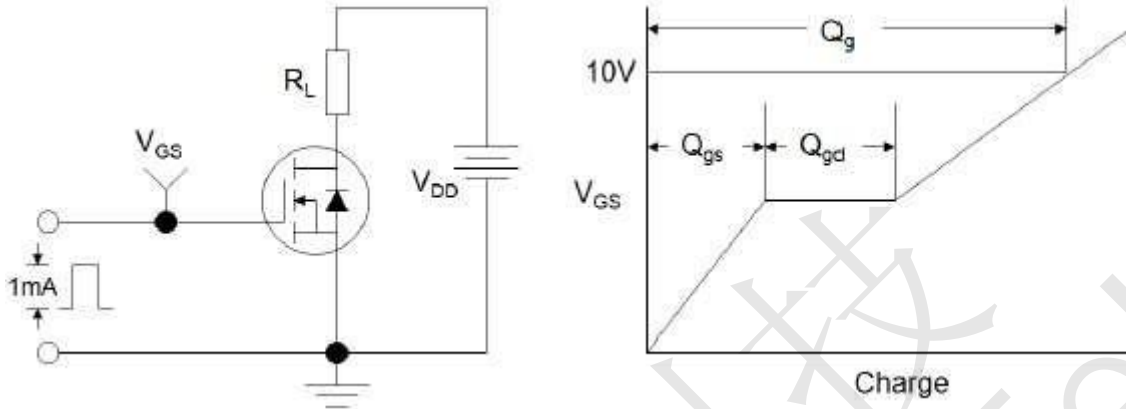


Figure1:Gate Charge Test Circuit & Waveform

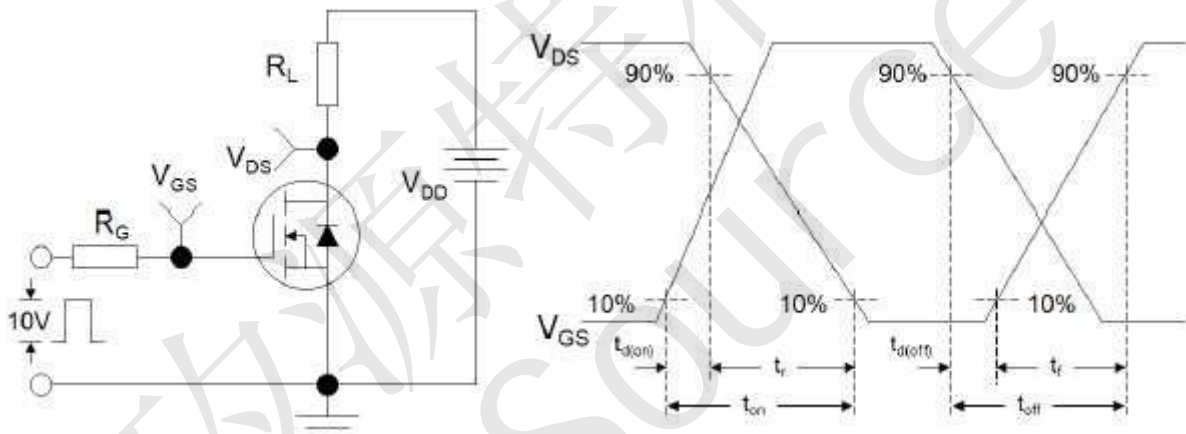


Figure 2: Resistive Switching Test Circuit & Waveforms

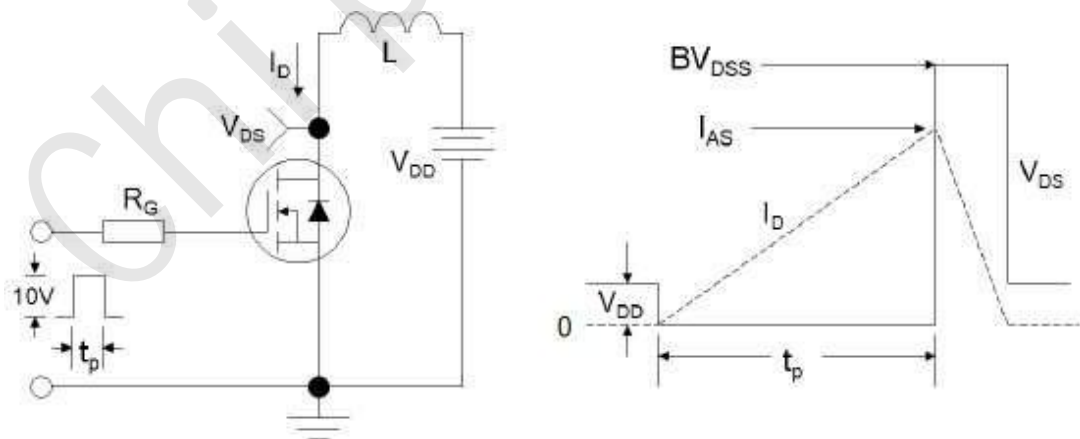
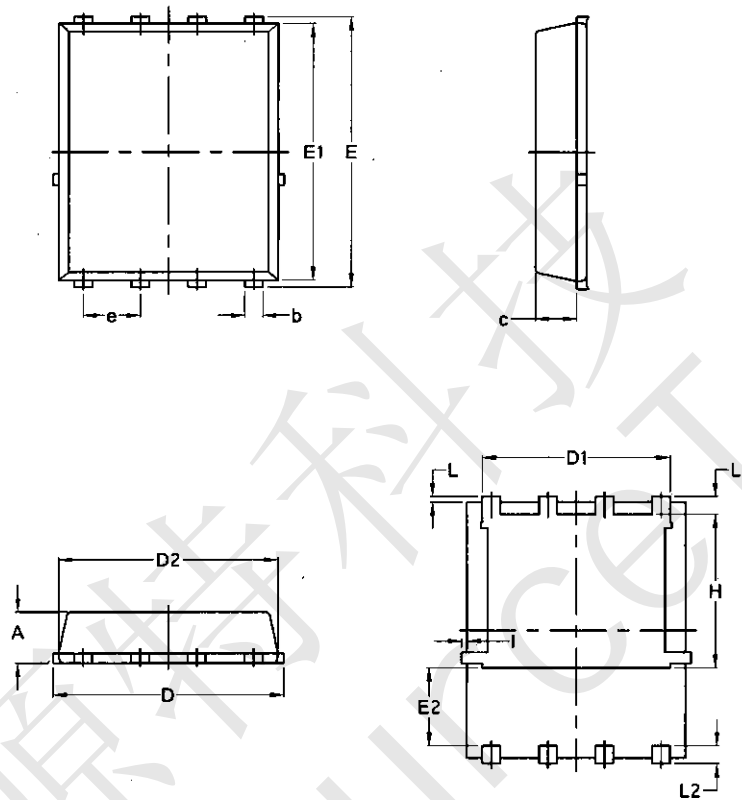


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



CST20N03D Package Mechanical Data-PDFN3*3-8L- Single



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | NOM | MAX |
|--------|-----------|------|------|
| A | 0.70 | 0.80 | 0.90 |
| A1 | 0.00 | 0.03 | 0.05 |
| b | 0.24 | 0.30 | 0.35 |
| c | 0.10 | 0.15 | 0.20 |
| D | 3.25 | 3.32 | 3.40 |
| D1 | 3.05 | 3.15 | 3.25 |
| D2 | 2.40 | 2.50 | 2.60 |
| E | 3.00 | 3.10 | 3.20 |
| E1 | 1.35 | 1.45 | 1.55 |
| e | 0.65 BSC. | | |
| H | 3.20 | 3.30 | 3.40 |
| L | 0.30 | 0.40 | 0.50 |
| L1 | 0.10 | 0.15 | 0.20 |
| L2 | 1.13 REF. | | |